

Serial No. To Be Assigned

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Park et al.	Examiner:	Unknown
Serial No.:	To Be Assigned	Group Art Unit:	To Be Assigned
Filed:	August 27, 2003	Docket No.:	01770.0002-US-01
Title:	SPLIT-GATE MEMORY CELL, MEMORY ARRAY INCORPORATING SAME, AND METHOD OF MANUFACTURE THEREOF		

CERTIFICATE UNDER 37 C.F.R. 1.10:

'Express Mail' mailing number: EV 314777172 US.

Date of Deposit: August 27, 2003

The undersigned hereby certifies that this Transmittal Letter and the paper or fee, as described herein, are being deposited with the United States Postal Service 'Express Mail Post Office To Addressee' service under 37 CFR 1.10 and is addressed to the Commissioner for Patents, Alexandria, VA 22313-1450.

By: _____

David H. Carroll

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT UNDER
37 C.F.R. §1.97(b)

Mail Stop PATENT APPLICATION
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicant(s) respectfully submit(s) the items of information on the enclosed Form 1449 for the attention of the Examiner in the above-identified application.

This Information Disclosure Statement is being filed within three months of the filing of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d); within three months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application; before the mailing date of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 C.F.R. 1.114. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

A copy of documents J and K listed on the enclosed Form 1449 are enclosed in accordance with 37 C.F.R. §1.98(a)(2). Copies of the other listed documents are not provided pursuant to the Office waiver as set forth in the Notice of July 11, 2003 entitled "Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003."

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§102 and 103. In addition, Applicant(s) do(es) not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended, and reserve the right to establish otherwise under 37 C.F.R. §1.131 or others.

Consideration of the items listed is respectfully requested. According to M.P.E.P. §609, Applicant(s) request(s) that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

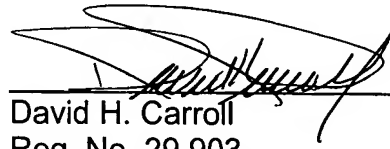
Authorization is hereby given to charge any additional fees or credit any overpayments that may be deemed necessary to Deposit Account Number 50-1038.

Respectfully submitted,

Altera Law Group, LLC
Customer No. 22865

Date: August 27, 2003

By:



David H. Carroll
Reg. No. 29,903
DHC/mar

INFORMATION DISCLOSURE STATEMENT
PTO Form 1449

Docket Number
01770.0002-US-01

Serial Number
To Be Assigned

Applicant(s)
Park et al.

Filing Date
August 26, 2003

Group Art Unit
To Be Assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE (IF APPROPRIATE)
	A	5,274,588	12/28/93	Manzur, et al.			
	B	5,494,838	02/27/96	Chang, et al.			
	C	5,508,955	04/16/96	Zimmer, et al.			
	D	6,013,552	01/11/00	Oyama			
	E	5,856,223	01/05/99	Wang			
	F	6,281,545	08/28/01	Liang, et al.			
	G	6,329,248	12/11/01	Yang			
	H	6,365,449	04/02/02	Kuo, et al.			
	I	6,538,276	03/25/03	Hsieh, et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS

	J	U.S. Patent Application Serial Number 10/358,645 entitled "VIRTUAL GROUND SINGLE TRANSISTOR MEMORY CELL, MEMORY ARRAY INCORPORATING SAME AND METHOD OF OPERATION THEREOF", filed February 4, 2003.
	K	Yamauchi, Yoshimitsu, et al., "A New Cell Structure for Sub-quarter Micron High Density Flash Memory", 1995 International Electron Devices Meeting TECHNICAL DIGEST, IEEE, pp. 267-270, December 10-13, 1995.

Examiner:

Date Considered: